



勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
Http://www.100y.com.tw

# STP310N10F7

N-channel 100 V, 2.3 mΩ typ., 180 A STripFET™ VII DeepGATE™ Power MOSFET in a TO-220 package

Datasheet — production data

## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STP310N10F7	100 V	2.7 mΩ	180 A

- Ultra low on-resistance
- 100% avalanche tested

## Applications

- High current switching applications

## Description

This device utilizes the 7<sup>th</sup> generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R<sub>DS(on)</sub> in all packages.

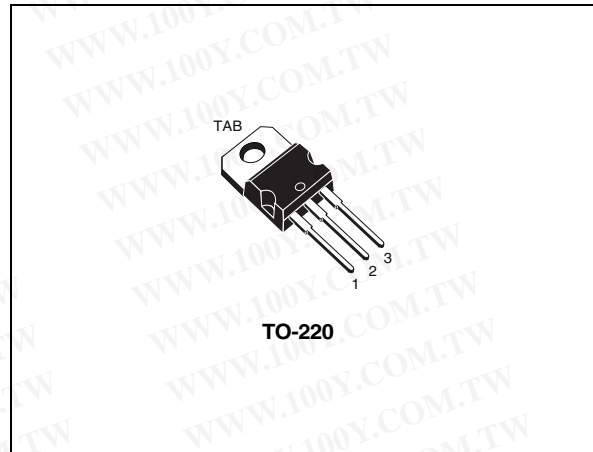


Figure 1. Internal schematic diagram

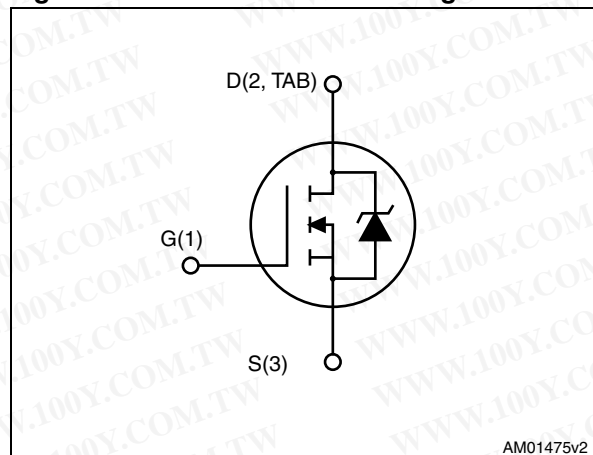


Table 1. Device summary

Order code	Marking	Package	Packaging
STP310N10F7	310N10F7	TO-220	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>19</b>
<b>6</b>	<b>Revision history</b> .....	<b>21</b>



# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	100	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	315	W
	Derating factor	2.1	W/ $^\circ\text{C}$
$T_j$ $T_{stg}$	Operating junction temperature storage temperature	- 55 to 175	$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area.

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.48	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified).

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 250\ \mu\text{A}$	100			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 100\ \text{V}$ $V_{DS} = 100\ \text{V}, T_C = 125\text{ °C}$			10 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\ \text{V}$			$\pm 200$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$		3.8		V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}, I_D = 60\ \text{A}$		2.3	2.7	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\ \text{V}, f = 1\ \text{MHz},$ $V_{GS} = 0$	-	12800	-	pF
$C_{oss}$	Output capacitance			3500		pF
$C_{rss}$	Reverse transfer capacitance			170		pF
$Q_g$	Total gate charge	$V_{DD} = 50\ \text{V}, I_D = 180\ \text{A},$ $V_{GS} = 10\ \text{V}$ (see <a href="#">Figure 14</a> )	-	180	-	nC
$Q_{gs}$	Gate-source charge			78		nC
$Q_{gd}$	Gate-drain charge			34		nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ \text{V}, I_D = 90\ \text{A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\ \text{V}$ (see <a href="#">Figure 13</a> , <a href="#">Figure 18</a> )	-	62	-	ns
$t_r$	Rise time			108		ns
$t_{d(off)}$	Turn-off delay time			148		ns
$t_f$	Fall time			40		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		180 720	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=60\text{ A}$ , $V_{GS}=0$	-		1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=180\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=80\text{ V}$ , $T_j=150^\circ\text{C}$ (see <a href="#">Figure 15</a> )	-	85 200 4.7		ns nC A

1. Pulse width limited by safe operating area.
2. Pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%



## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

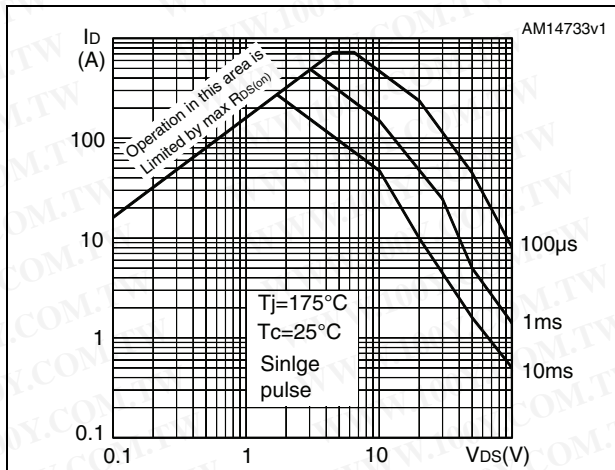


Figure 3. Thermal impedance

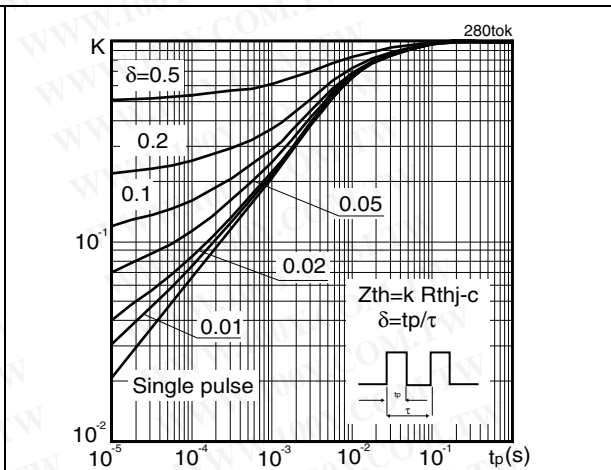


Figure 4. Output characteristics

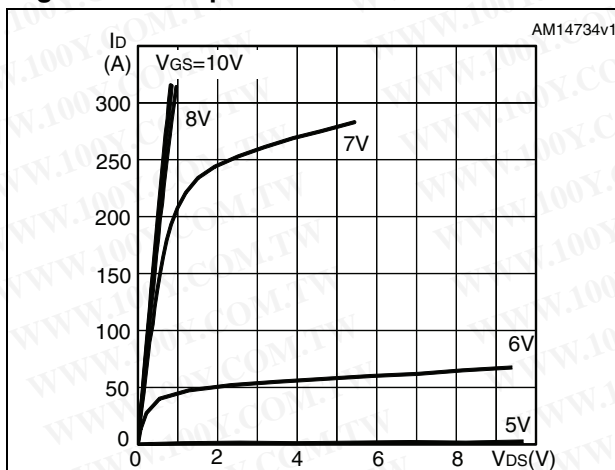


Figure 5. Transfer characteristics

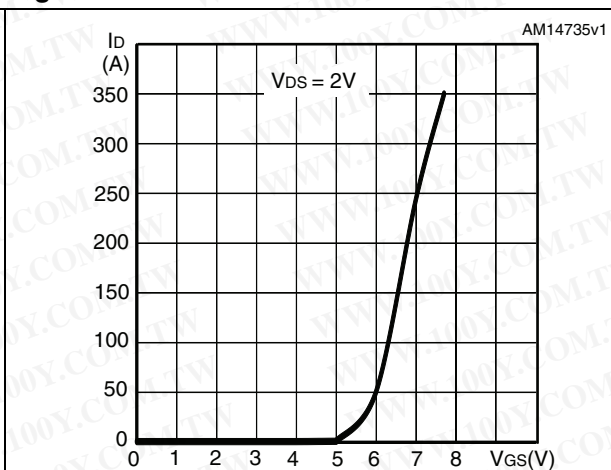


Figure 6. Gate charge vs gate-source voltage

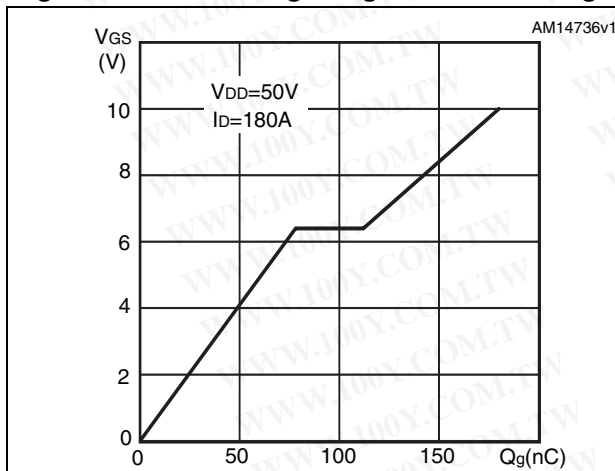


Figure 7. Static drain-source on-resistance

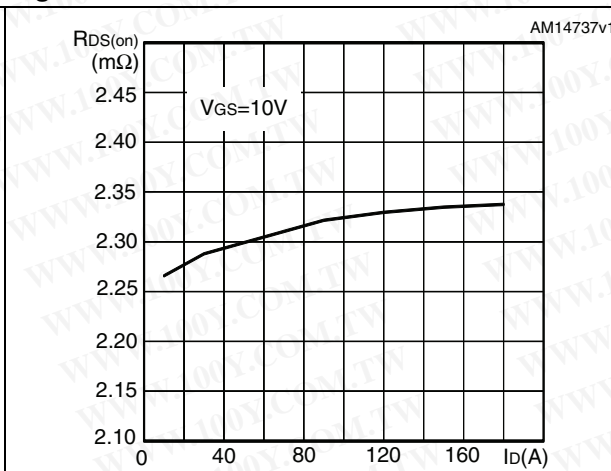


Figure 8. Capacitance variations

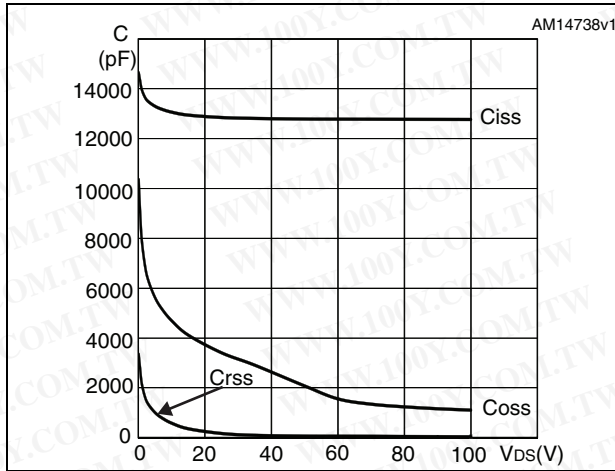


Figure 9. Source-drain diode forward characteristics

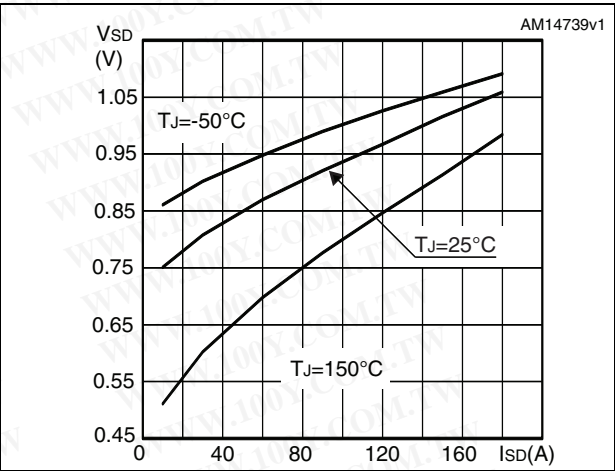


Figure 10. Normalized gate threshold voltage vs temperature

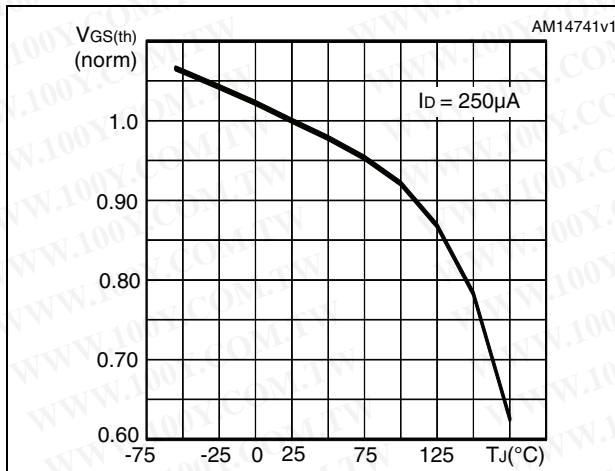


Figure 11. Normalized on-resistance vs temperature

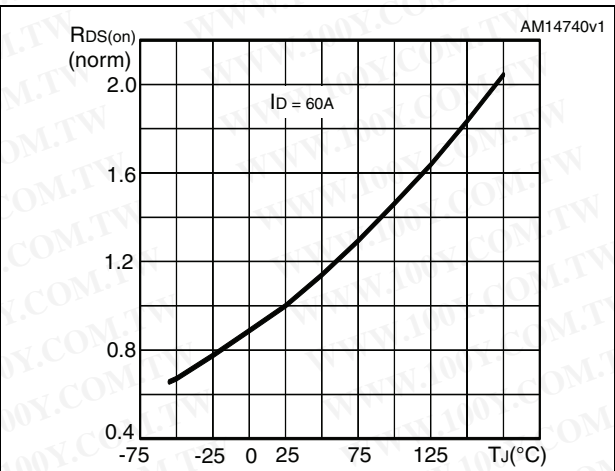
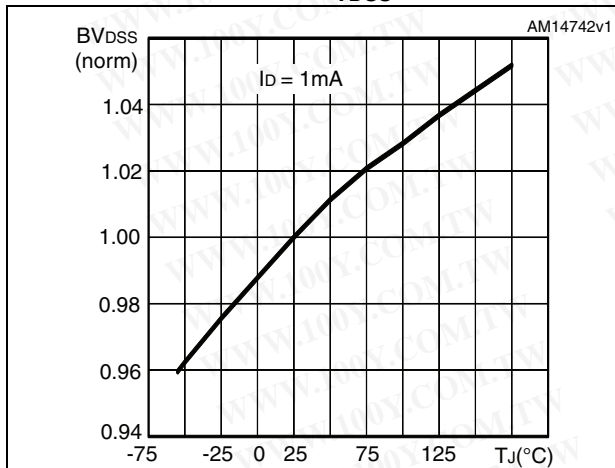
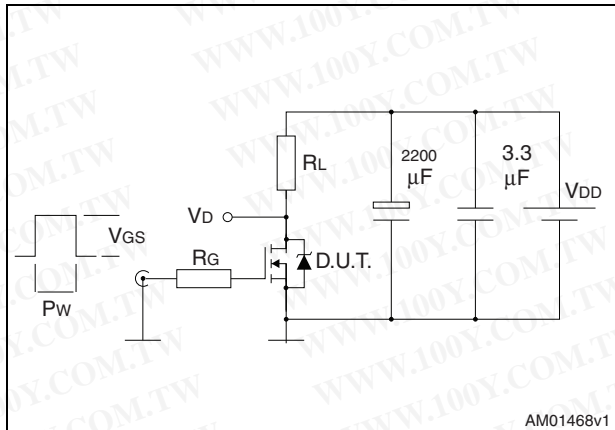


Figure 12. Normalized BV<sub>DSS</sub> vs temperature



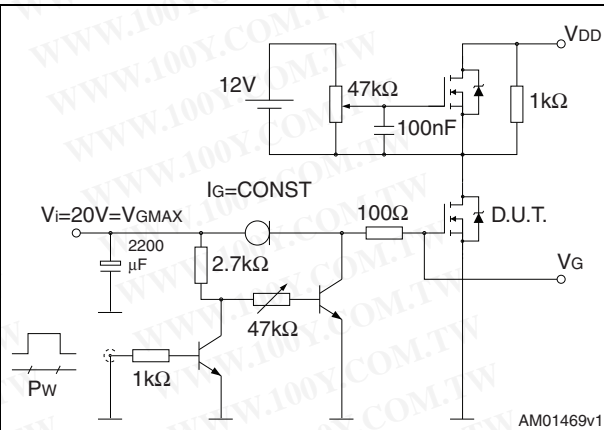
### 3 Test circuits

Figure 13. Switching times test circuit for resistive load



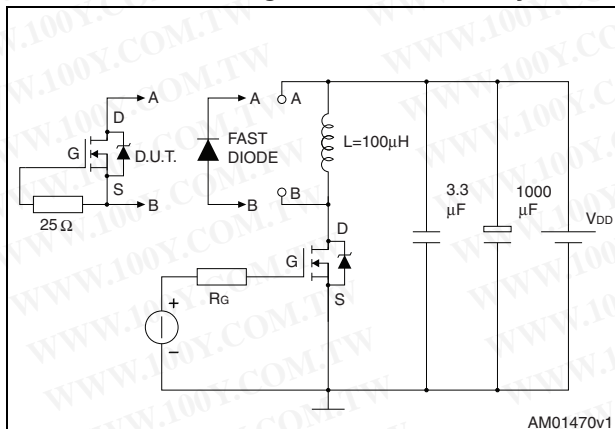
AM01468v1

Figure 14. Gate charge test circuit



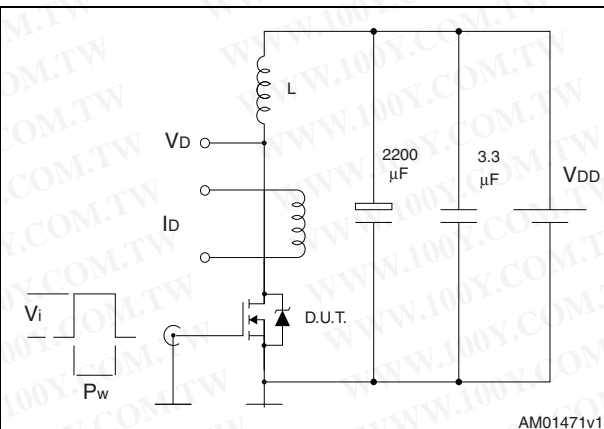
AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



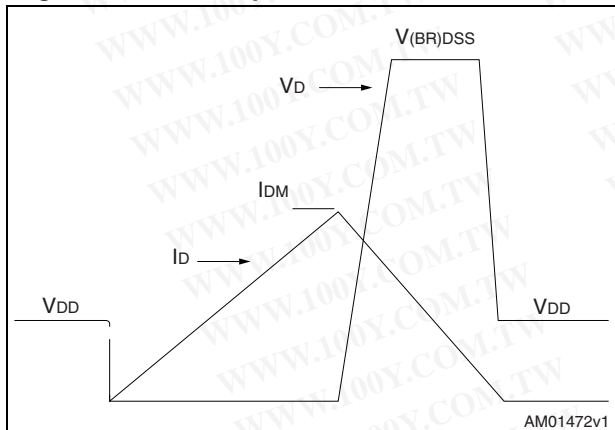
AM01470v1

Figure 16. Unclamped inductive load test circuit



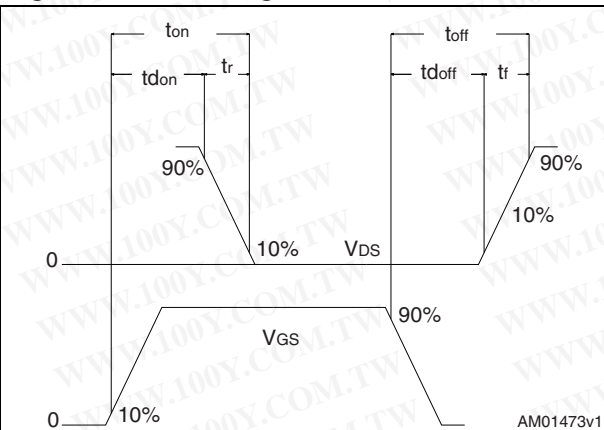
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1



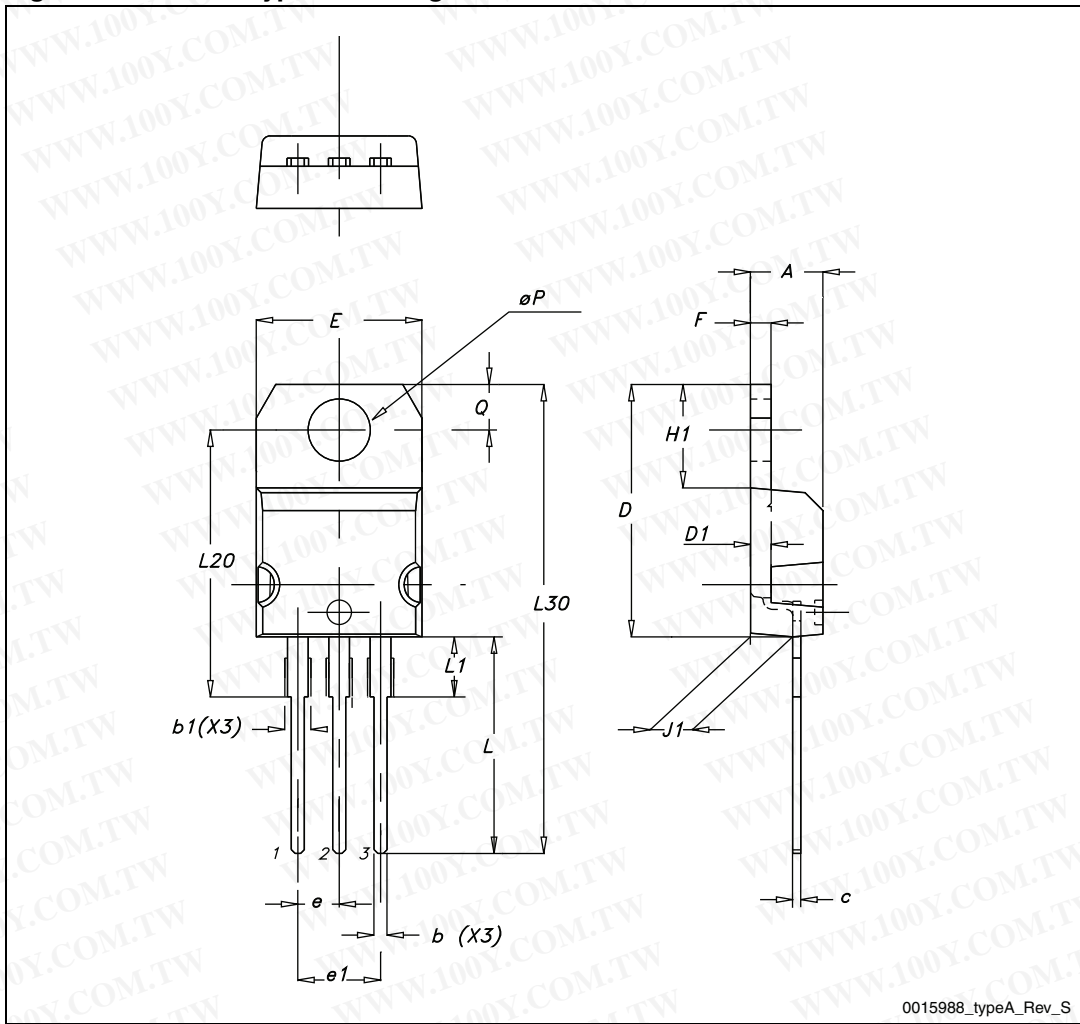
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
19-Oct-2011	1	Initial version.
21-Dec-2011	2	Updated title and description in cover page.
06-Mar-2012	3	Updated $I_D$ value at $T_C = 25^\circ\text{C}$ in the whole document. <a href="#">Table 5</a> , <a href="#">Table 6</a> and <a href="#">Table 7</a> have been updated with typical values.
20-Aug-2012	4	Document status promoted from preliminary to production data. Added <a href="#">Section 2.1: Electrical characteristics (curves)</a> . Minor text changes.
31-Oct-2012	5	– Added: H <sup>2</sup> PAK-2 and H <sup>2</sup> PAK-6 packages – Updated: <a href="#">Section 4: Package mechanical data</a> and <a href="#">Section 4: Package mechanical data</a> – Minor text changes
07-Dec-2012	6	– Minor text changes – The part numbers STH310N10F7-2, STH310N10F7-6 have been moved to a separate datasheet

勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
Http://www.100y.com.tw

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)

